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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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ATTY, DOCKET NO. SEPP15,001AUS APPLICATION NO. 10/003,749 APPLICANT Skarp et al. FILING DATE GROUP October 23, 2001 1762

	U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
W/7	1	US 2003/0129298 A1	07/10/03	Tera et al.			
	2	US 2001/0031379 A1	10/18/01	Tera et al.			
	3	US 2002/0003403 A1	01/10/02	Ghosh et al.	Y		
	4	US 2001/0052752 A1	12/20/01	Ghosh et al.	2 1		

			FOREIGN PATENT DOCUMENTS	0			
EXAMINER	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
INITIAL						YES	NO
5	WO 03/008110 A1	01/30/03	PCT				

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
M	6	Kukli et al, "Atomic layer epitaxy growth of aluminum oxide thin films from a novel Al(CH3)2Cl precursor and H2O.", J. Vac. Sci. Technol. A 15(4), July/Aug 1997, pp. 2214-2218
	7	Hiltunen et al. "Growth and Characterization of Aluminum Oxide Thin Films Deposited from Various Source Materials by Atomic Layer Epitaxy and Chemical Vapor Deposition Processes", Materials Chemistry and Physics, 28 (1991) pp. 379-388
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EXAMINER DATE CONSIDERED

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